

PolarHV™ HiPerFET IXFN 64N50P

Power MOSFET

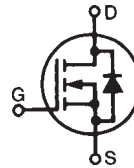
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

$$V_{DSS} = 500 \text{ V}$$

$$I_{D25} = 61 \text{ A}$$

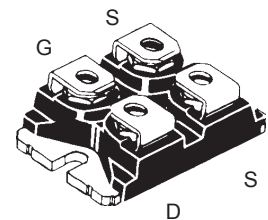
$$R_{DS(on)} \leq 85 \text{ m}\Omega$$

$$t_{rr} \leq 200 \text{ ns}$$



| Symbol | Test Conditions | Maximum Ratings | |
|---------------|---|------------------|------------------------|
| | | | |
| V_{DSS} | $T_J = 25^\circ\text{C}$ to 150°C | 500 | V |
| V_{DGR} | $T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$ | 500 | V |
| V_{GSS} | Continuous | ± 30 | V |
| V_{GSM} | Transient | ± 40 | V |
| I_{D25} | $T_C = 25^\circ\text{C}$ | 61 | A |
| I_{DM} | $T_C = 25^\circ\text{C}$, pulse width limited by T_{JM} | 150 | A |
| I_{AR} | $T_C = 25^\circ\text{C}$ | 64 | A |
| E_{AR} | $T_C = 25^\circ\text{C}$ | 80 | mJ |
| E_{AS} | $T_C = 25^\circ\text{C}$ | 2.5 | J |
| dv/dt | $I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$, $R_G = 4 \Omega$ | 20 | V/ns |
| P_D | $T_C = 25^\circ\text{C}$ | 700 | W |
| T_J | | -55 ... +150 | $^\circ\text{C}$ |
| T_{JM} | | 150 | $^\circ\text{C}$ |
| T_{stg} | | -55 ... +150 | $^\circ\text{C}$ |
| T_L | 1.6 mm (0.062 in.) from case for 10 s | 300 | $^\circ\text{C}$ |
| V_{ISOL} | 50/60 Hz $t = 1 \text{ min}$ $I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$ | 2500 3000 | V~ V~ |
| M_d | Mounting torque Terminal connection torque (M4) | 1.5/13 1.5/13 | Nm/lb.in. Nm/lb.in. |
| Weight | | 30 | g |

miniBLOC, SOT-227 B (IXFN)
E153432



G = Gate D = Drain
S = Source

Either Source terminal S can be used as the Source terminal or the Kelvin Source (gate return) terminal.

Features

- International standard package
- Encapsulating epoxy meets UL 94 V-0, flammability classification
- miniBLOC with Aluminium nitride isolation
- † Fast recovery diode
- † Unclamped Inductive Switching (UIS) rated
- † Low package inductance
- easy to drive and to protect

Advantages

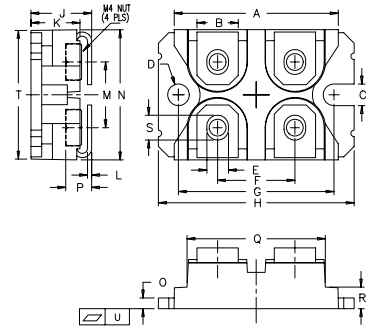
- † Easy to mount
- † Space savings
- † High power density

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|--|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$ | 500 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 8 \text{ mA}$ | 3.0 | | 5.5 V |
| I_{GSS} | $V_{GS} = \pm 30 \text{ V}_{DC}$, $V_{DS} = 0$ | | | $\pm 200 \text{ nA}$ |
| I_{DSS} | $V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$ | | | 25 μA 1000 μA |
| $R_{DS(on)}$ | $V_{GS} = 10 \text{ V}$, $I_D = 32 \text{ A}$, Note 1 | | | 85 $\text{m}\Omega$ |

| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$ unless otherwise specified) | | |
|--------------|---|---|------|--------------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 20\text{ V}; I_D = 32\text{ A}$, Note 1 | 30 | 50 | S |
| C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$ | | 8700 | pF |
| C_{oss} | | | 970 | pF |
| C_{rss} | | | 90 | pF |
| $t_{d(on)}$ | $V_{DS} = 0.5 V_{DSS}, V_{GS} = 10\text{ V}$ $I_D = 32\text{ A}, R_G = 2\ \Omega$ (External) | | 30 | ns |
| t_r | | | 25 | ns |
| $t_{d(off)}$ | | | 85 | ns |
| t_f | | | 22 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = I_T$ | | 150 | nC |
| Q_{gs} | | | 50 | nC |
| Q_{gd} | | | 50 | nC |
| R_{thJC} | | | | $0.18\ ^\circ\text{C/W}$ |
| R_{thCS} | | 0.05 | | $^\circ\text{C/W}$ |

| Source-Drain Diode | | Characteristic Values ($T_J = 25^\circ\text{C}$ unless otherwise specified) | | |
|--------------------|--|---|------|---------------|
| Symbol | Test Conditions | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0\text{ V}$ | | | 64 A |
| I_{SM} | Repetitive | | | 150 A |
| V_{SD} | $I_F = I_S, V_{GS} = 0\text{ V}$, Note 1 | | | 1.5 V |
| t_{rr} | $I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$ | | | 200 ns |
| Q_{RM} | | | 0.6 | μC |
| I_{RM} | | | 6 | A |

SOT-227B Outline



| SYM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 1.240 | 1.255 | 31.50 | 31.88 |
| B | .307 | .323 | 7.80 | 8.20 |
| C | .161 | .169 | 4.09 | 4.29 |
| D | .161 | .169 | 4.09 | 4.29 |
| E | .161 | .169 | 4.09 | 4.29 |
| F | .587 | .595 | 14.91 | 15.11 |
| G | 1.186 | 1.193 | 30.12 | 30.30 |
| H | 1.496 | 1.505 | 38.00 | 38.23 |
| J | .460 | .481 | 11.68 | 12.22 |
| K | .351 | .378 | 8.92 | 9.60 |
| L | .030 | .033 | 0.76 | 0.84 |
| M | .496 | .506 | 12.60 | 12.85 |
| N | .990 | 1.001 | 25.15 | 25.42 |
| O | .078 | .084 | 1.98 | 2.13 |
| P | .195 | .235 | 4.95 | 5.97 |
| Q | 1.045 | 1.059 | 26.54 | 26.90 |
| R | .155 | .174 | 3.94 | 4.42 |
| S | .186 | .191 | 4.72 | 4.85 |
| T | .968 | .987 | 24.59 | 25.07 |
| U | -.002 | .004 | -0.05 | 0.1 |

Notes:

- 1) Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$

Fig. 1. Output Characteristics
@ 25°C

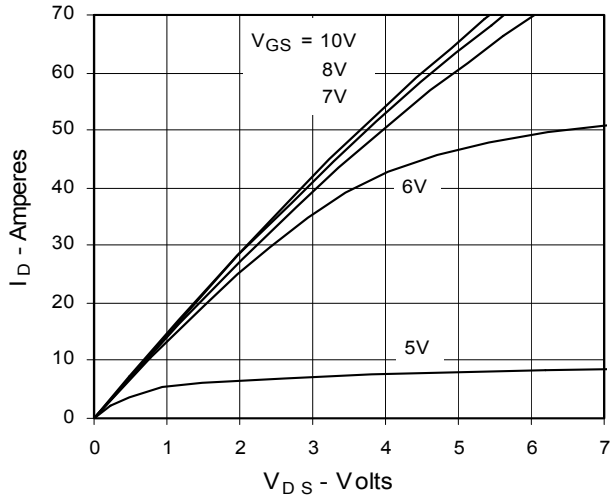


Fig. 2. Extended Output Characteristics
@ 25°C

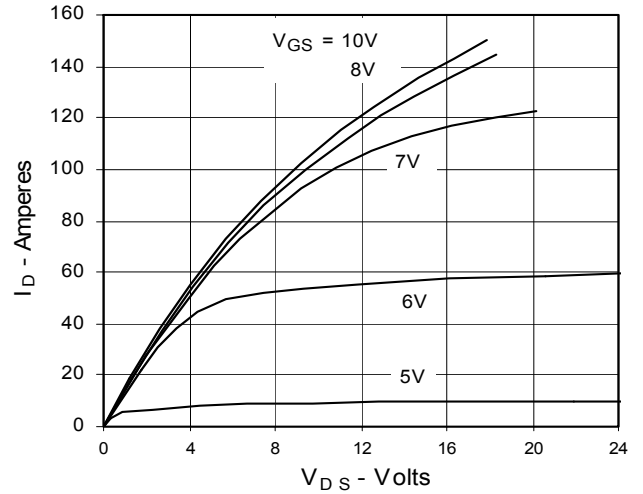


Fig. 3. Output Characteristics
@ 125°C

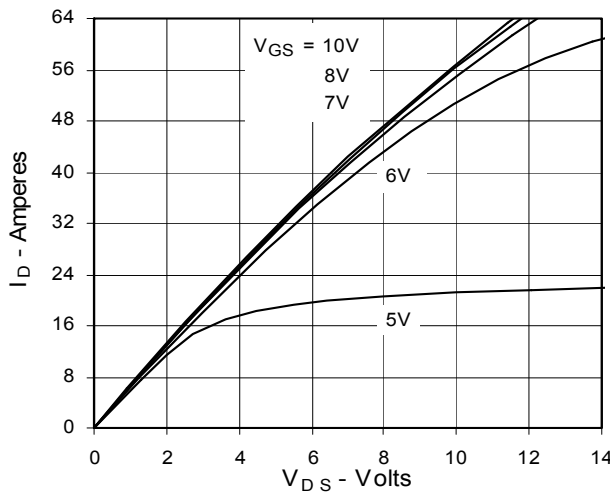


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 32A$ Value vs. Junction Temperature

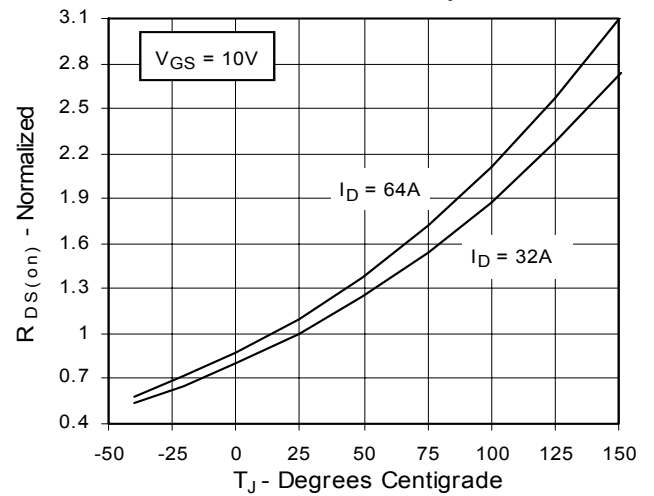


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 32A$ Value vs. Drain Current

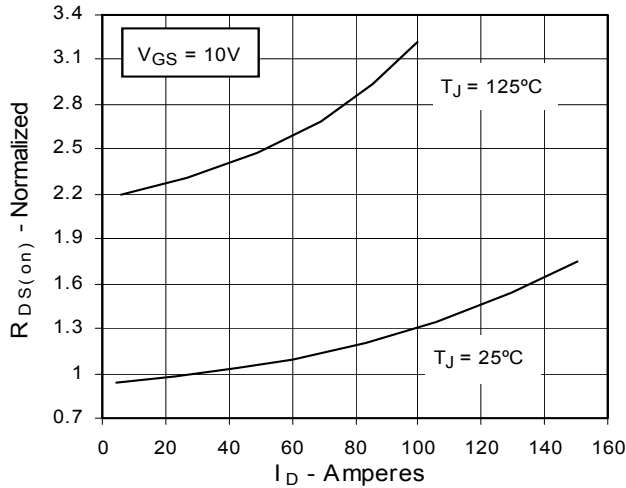


Fig. 6. Drain Current vs. Case Temperature

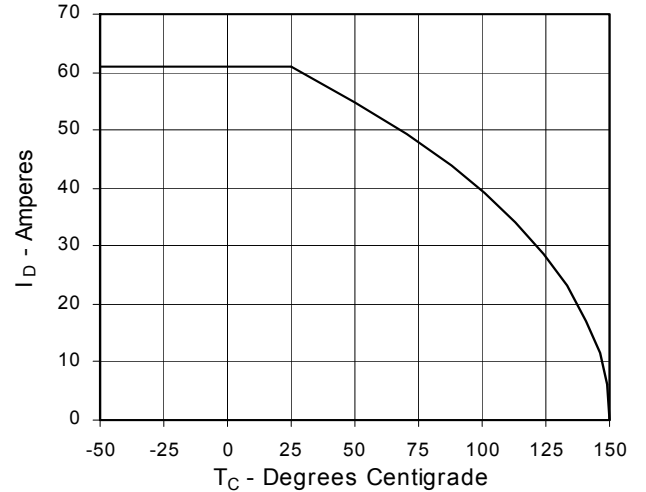


Fig. 7. Input Admittance

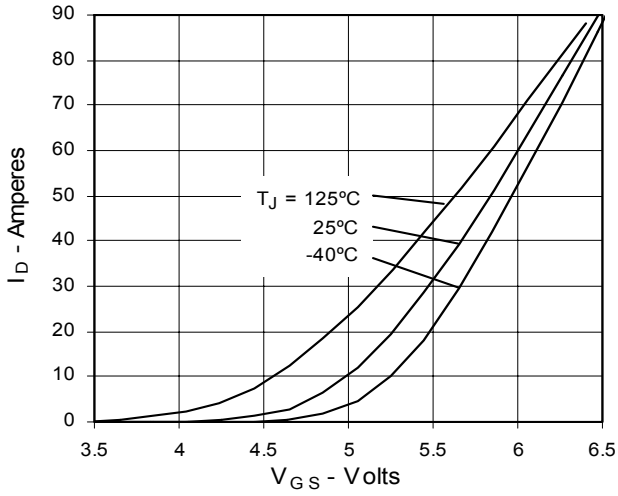


Fig. 8. Transconductance

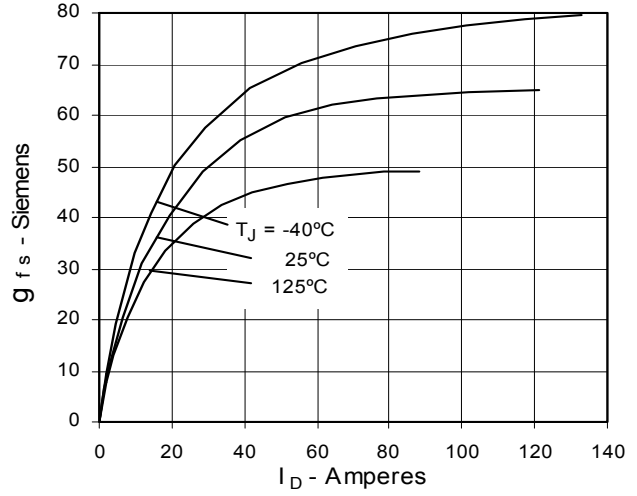


Fig. 9. Source Current vs. Source-To-Drain Voltage

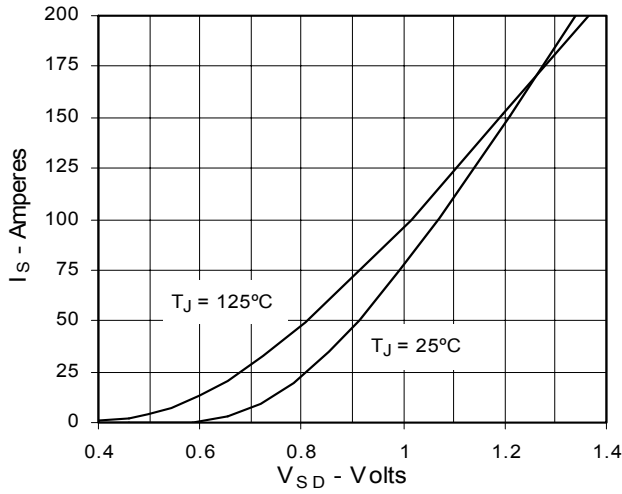


Fig. 10. Gate Charge

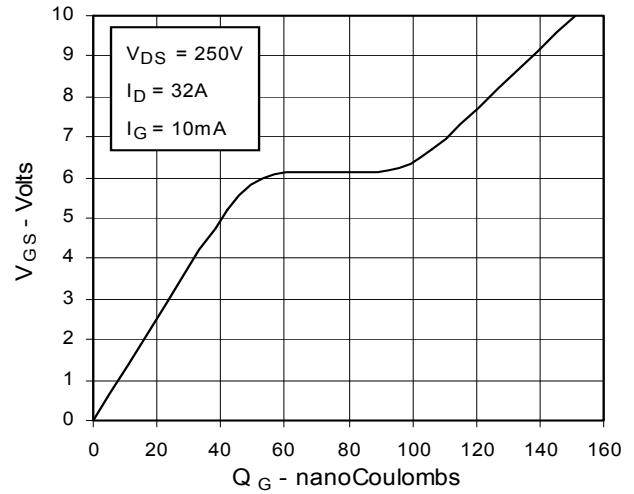


Fig. 11. Capacitance

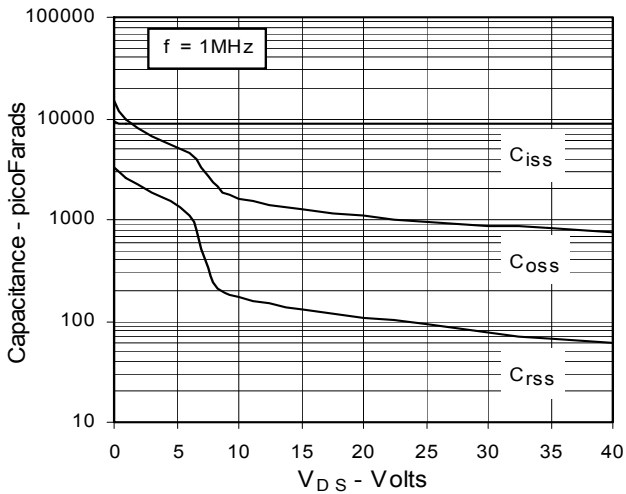
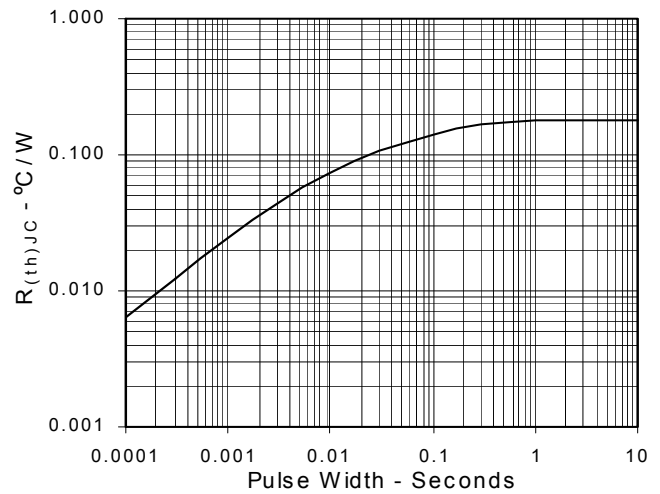


Fig. 12. Maximum Transient Thermal Resistance



Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[IXYS:](#)

[IXFN64N50P](#)